

Amendments to the Claims

Claims 1-43 (cancelled).

Claim 44 (new): A method of forming interconnect lines, comprising:

etching a series of intersecting horizontal and vertical trenches within a surface of a first material;

providing insulative material to within the trenches to define a first grid, the first grid isolating at least portions of the first material;

removing portions of the insulative material and depositing a second material to define a second grid within the first grid, the second grid comprising the second material; and

removing selected portions of the second material to define interconnect lines within the first grid.

Claim 45 (new): The method of claim 44, wherein both the first and second materials comprise semiconductive materials.

Claim 46 (new): The method of claim 45 wherein the composition of the first material is different than the composition of the second material.

Claim 47 (new): The method of claim 44 wherein the first material is comprised by a semiconductive material having a nitride-containing material thereover.

Claim 48 (new): The method of claim 47 wherein:

the semiconductive material comprises silicon; and

the nitride-containing material comprises Si_3N_4 .

Claim 49 (new): The method of claim 47 wherein the first material is supported by an oxide-comprising material, and the forming of the trenches within the surface of the first material exposes a surface of the oxide-comprising material.

Claim 50 (new): The method of claim 44 wherein, prior to depositing the second material to define the second grid within the first grid, at least a portion of both the first material and second material are coplanarized.

Claim 51 (new): The method of claim 44, wherein the removing portions of the insulative material comprises etching into the first grid to define a network of outwardly-exposed trenches running within the first grid.

Claim 52 (new): The method of claim 51, wherein the depositing the second material to define the second grid within the isolation grid comprises:

forming the second material within and over the trenches to a degree sufficient to completely fill the trenches; and

planarizing the second material to isolate second material within the trenches and to define the second grid.